

NPN PRE-BIASED TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Complementary PNP Types Available (DDTA)
- **Built-In Biasing Resistors**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

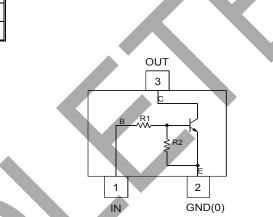
Part Number	R1 (NOM)	R2 (NOM)	Marking
DDTC122LE	0.22kΩ	10kΩ	N81
DDTC142JE	0.47kΩ	10kΩ	N82
DDTC122TE	0.22kΩ	OPEN	N83
DDTC142TE	0.47kΩ	OPEN	N84

Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.002 grams (Approximate)



Top View



Schematic and Pin Diagram

Ordering Information (Note 4)

Part Number	Compliance	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DDTC122LE-7-F	AEC-Q101	7	8	3,000
DDTC142JE-7-F	AEC-Q101	7	8	3,000
DDTC122TE-7-F	AEC-Q101	7	8	3,000
DDTC142TE-7-F	AEC-Q101	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:

SOT523	
Nxx YM	

Nxx = Product Type Marking Code (See Table in Features) YM = Date Code Marking Y or \overline{Y} = Year (ex: I = 2021) M or \overline{M} = Month (ex: 9 = September)

Date Code Key												
Year	2018	2019	20	20	2021	2022	2023	2024	20	25	2026	2027
Code	F	G	ł	4	I	J	K	L	1	N	Ν	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



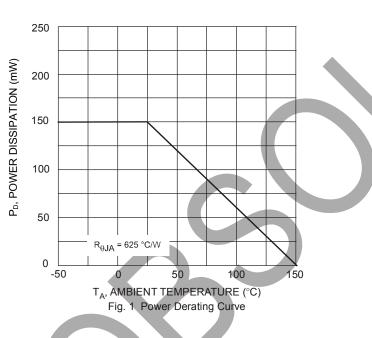
Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteris	stic	Symbol	Value	Unit
Supply Voltage, (3) to (2)		Vcc	50	V
Input Voltage, (1) to (2)	DDTC122LE DDTC142JE	V _{IN}	-5 to +6 -5 to +6	V
Input Voltage, (2) to (1)	DDTC122TE DDTC142TE	V _{EBO (MAX)}	5	V
Output Current	All	Ι _C	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Ilnit
Cildiacteristic	Symbol	Value	Unit
Power Dissipation	PD	150	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	R ₀ JA	625	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Note 5: Mounted on FR-4 PC Board with minimum recommended pad layout.





Electrical Characteristics R1, R2 Types (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Мах	Unit	Test Condition
	DDTC122LE DDTC142JE	VI(OFF)	0.3 0.3		_	V	V _{CC} = 5V, I _O = 100µA
Input Voltage	DDTC122LE DDTC142JE	V _{I(ON)}	_	_	2.0 2.0		$V_0 = 0.3V$, $I_0 = 20mA$ $V_0 = 0.3V$, $I_0 = 20mA$
Output Voltage		V _{O(ON)}	_		0.3	V	I _O /I _I = 5mA/0.25mA
Input Current	DDTC122LE DDTC142JE	h	_	_	28 13	mA	V _I = 5V
Output Current		I _{O(OFF)}			0.5	μA	$V_{CC} = 50V, V_{I} = 0V$
DC Current Gain	DDTC122LE DDTC142JE	GI	56 56				V _O = 5V, I _O = 10mA
Gain-Bandwidth Product (Note 6)		f _T	_	200	_	MHz	V _{CE} = 10V, I _E = 5mA, f = 100MHz

Electrical Characteristics R1- Only Type (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Мах	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	50			V	I _C = 50μA
Collector-Emitter Breakdown Voltag	е	BV _{CEO}	40			V	I _C = 1mA
Emitter-Base Breakdown Voltage	DDTC122TE DDTC142TE	BV _{EBO}	5	_	_	V	I _E = 50μΑ I _E = 50μΑ
Collector Cutoff Current		I _{CBO}	_		0.5	μA	V _{CB} = 50V
Emitter Cutoff Current	DDTC122TE DDTC142TE	I _{EBO}	_	_	0.5 0.5	μA	V _{EB} = 4V
Collector-Emitter Saturation Voltage		V _{CE(SAT)}	_		0.3	V	I _C = 5mA, I _B = 0.25mA
DC Current Transfer Ratio	DDTC122TE DDTC142TE	h _{FE}	100 100	250 250	600 600	_	I _C = 1mA, V _{CE} = 5V
Gain-Bandwidth Product (Note 6)		fT	_	200		MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz
Note 6: Transistor For Beforence	audu .			•		•	

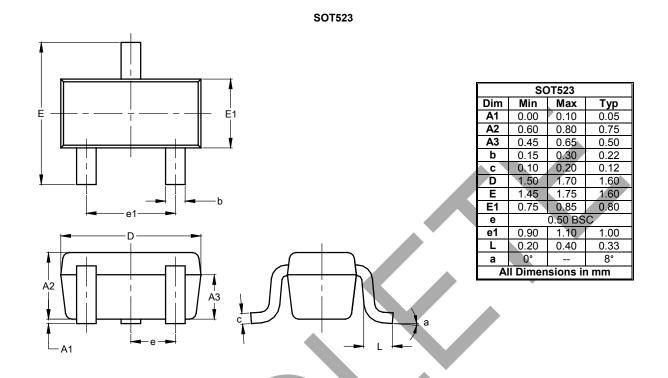
Note 6: Transistor – For Reference only,





Package Outline Dimensions

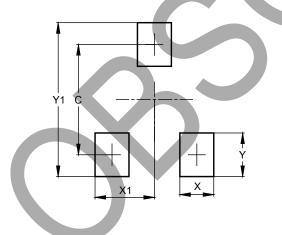
Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
С	1.29
Х	0.40
X1	0.70
Y	0.51
Y1	1.80



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